

# MMBTA55LT1, MMBTA56LT1

MMBTA56LT1 is a Preferred Device

## Driver Transistors

### PNP Silicon

#### Features

- Pb-Free Package is Available

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MMBTA55 MMBTA56	$V_{CE0}$	-60 -80	Vdc
Collector–Base Voltage MMBTA55 MMBTA56	$V_{CBO}$	-60 -80	Vdc
Emitter–Base Voltage	$V_{EBO}$	-4.0	Vdc
Collector Current – Continuous	$I_C$	-500	mAdc

#### THERMAL CHARACTERISTICS

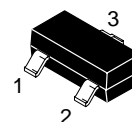
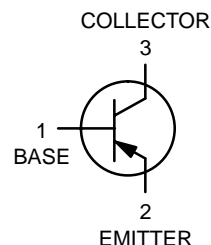
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

- FR–5 =  $1.0 \times 0.75 \times 0.062$  in.
- Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



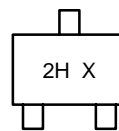
ON Semiconductor®

<http://onsemi.com>

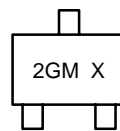


SOT–23  
CASE 318  
STYLE 6

#### MARKING DIAGRAMS



MMBTA55LT1



MMBTA56LT1

2H, 2GM = Specific Device Code  
X = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBTA55LT1	SOT–23	3000/Tape & Reel
MMBTA55LT3	SOT–23	10,000/Tape & Reel
MMBTA56LT1	SOT–23	3000/Tape & Reel
MMBTA56LT1G	SOT–23 (Pb–Free)	3000/Tape & Reel
MMBTA56LT3	SOT–23	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

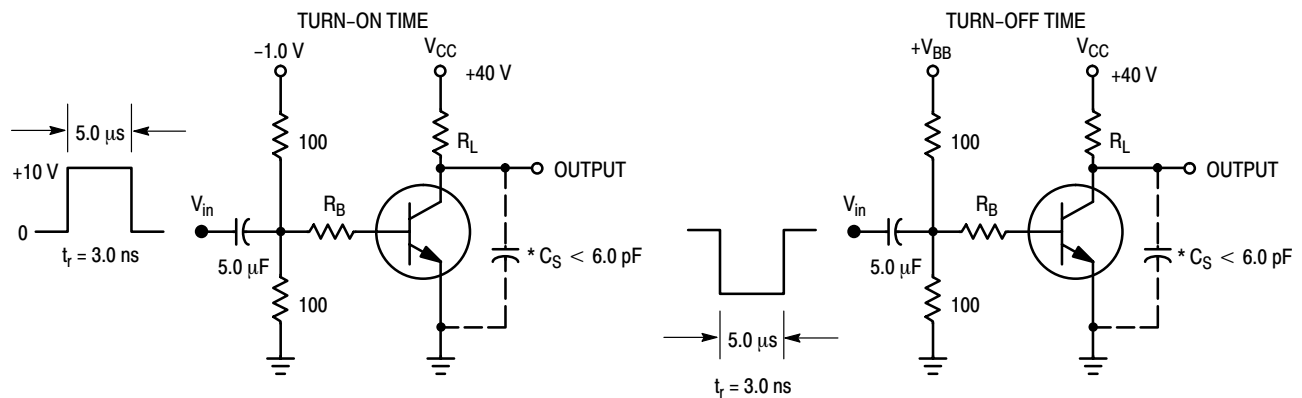
Preferred devices are recommended choices for future use and best overall value.

# MMBTA55LT1, MMBTA56LT1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 3) ( $I_C = -1.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-60 -80	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -100\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-4.0	-	Vdc
Collector Cutoff Current ( $V_{CE} = -60\text{ Vdc}$ , $I_B = 0$ )	$I_{CES}$	-	-0.1	$\mu\text{A}$ dc
Collector Cutoff Current ( $V_{CB} = -60\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = -80\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	- -	-0.1 -0.1	$\mu\text{A}$ dc
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = -10\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ ) ( $I_C = -100\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ )	$h_{FE}$	100 100	- -	-
Collector–Emitter Saturation Voltage ( $I_C = -100\text{ mA}$ , $I_B = -10\text{ mA}$ )	$V_{CE(sat)}$	-	-0.25	Vdc
Base–Emitter On Voltage ( $I_C = -100\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ )	$V_{BE(on)}$	-	-1.2	Vdc
<b>SMALL–SIGNAL CHARACTERISTICS</b>				
Current–Gain – Bandwidth Product (Note 4) ( $I_C = -100\text{ mA}$ , $V_{CE} = -1.0\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	50	-	MHz

3. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .  
 4.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.



\*Total Shunt Capacitance of Test Jig and Connectors  
 For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

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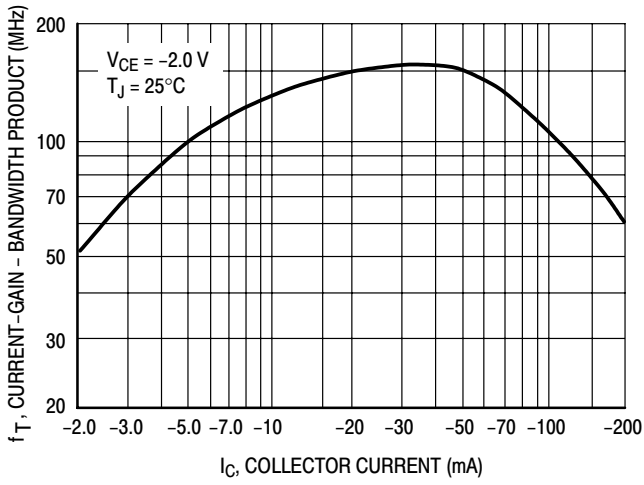


Figure 2. Current-Gain — Bandwidth Product

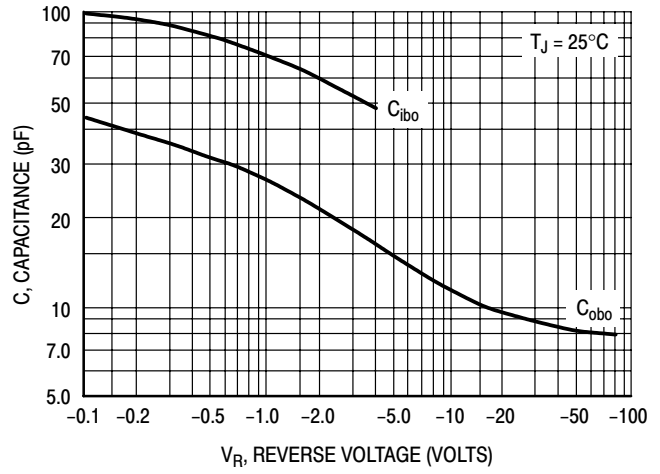


Figure 3. Capacitance

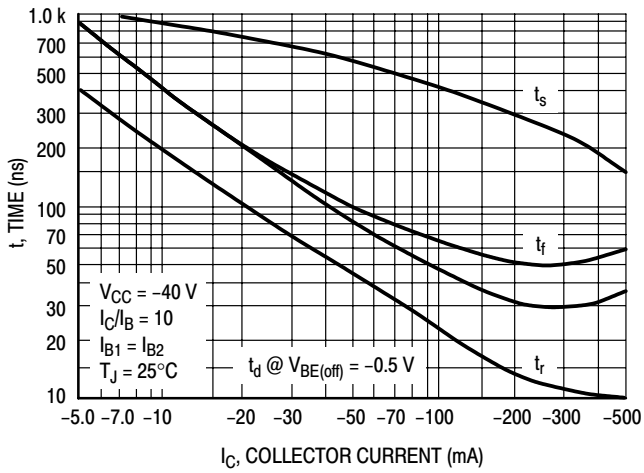


Figure 4. Switching Time

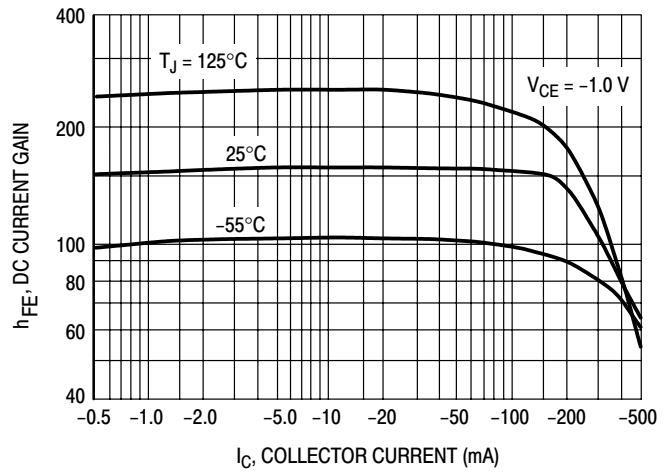


Figure 5. DC Current Gain

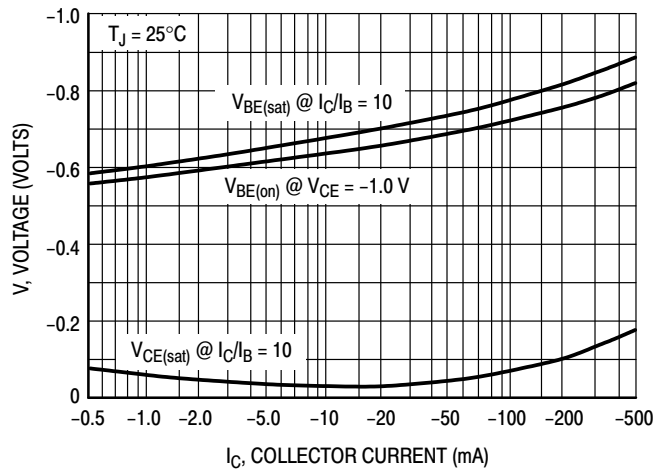


Figure 6. "ON" Voltages

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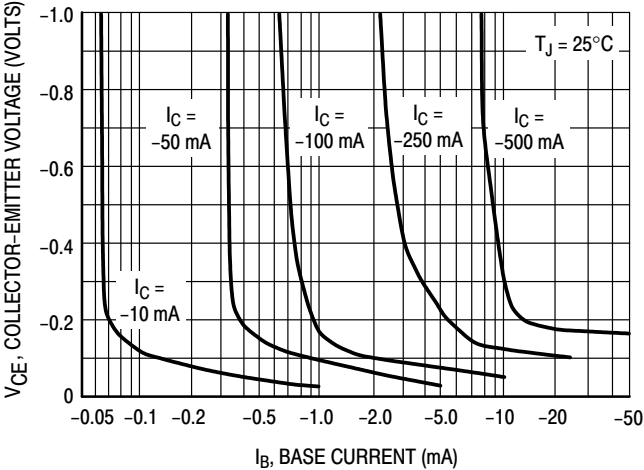


Figure 7. Collector Saturation Region

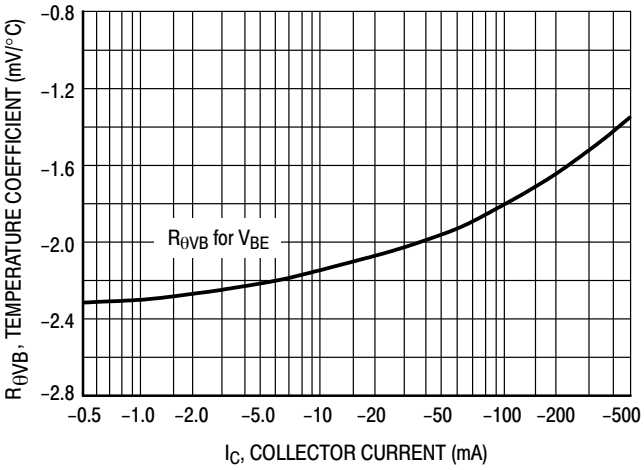
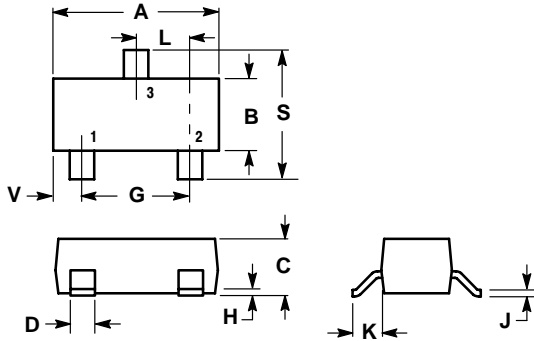


Figure 8. Base-Emitter Temperature Coefficient

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## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AH



NOTES:

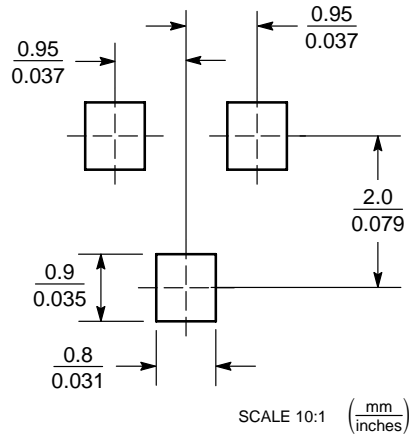
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

### SOLDERING FOOTPRINT\*



### SOT-23

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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